

Appl. No. 09/920,978

**Amendments to the Claims**

Claims 1-8 (cancelled).

9. (Previously presented) The method of claim 16 wherein the etching comprises magnetically enhanced plasma etching.

Claims 10-13 (Cancelled).

14. (Previously presented) The method of claim 16 wherein the etching chemistry comprises at least two fluorocarbons.

15. (Previously presented) The method of claim 16 wherein the etching chemistry comprises at least three fluorocarbons.

16. (Currently amended) A method of forming integrated circuitry comprising:  
forming a layer of oxide material over a semiconductor substrate;  
forming a layer comprising silicon nitride layer over the layer of oxide material;  
forming a patterned photoresist comprising masking layer over the silicon nitride layer, the patterned masking layer comprising mask openings therethrough; and  
etching an opening through the silicon nitride ~~comprising~~ layer, through the layer of oxide material and into a semiconductive material of the semiconductor substrate, the etching occurring through the mask openings substantially selectively to the photoresist

Appl. No. 09/920,978

comprising layer using a single etching chemistry produced by generating a plasma from a processing gas consisting of ~~ammonia~~, ammonia and at least one fluorocarbon selected from the group consisting of  $\text{CF}_4$ ,  $\text{C}_4\text{F}_6$ ,  $\text{C}_4\text{F}_8$ ,  $\text{C}_2\text{F}_6$ ,  $\text{C}_3\text{F}_8$ ,  $\text{C}_5\text{F}_8$ , and chlorofluorocarbons, the etching being conducted under etching conditions effective to substantially anisotropically etch the silicon nitride comprising layer, the etching chemistry comprising a volumetric ratio of all fluorocarbon to the ammonia of from 40:1 to 20:1 and providing increased selectivity to the photoresist comprising masking layer than would otherwise occur using identical etching chemistry and identical etching conditions without any ammonia.

Claims 17-46 (Cancelled).

47. (Previously presented) The method of claim 16 wherein the photoresist comprises 193 nanometer photoresist.

48. (Previously presented) The method of claim 16 comprising introducing the ammonia and fluorocarbon successively into a reaction chamber in which the substrate is received during the etching and generating the plasma within the reaction chamber.

49. (Previously presented) The method of claim 16 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

**Appl. No. 09/920,978**

**Claims 50-66. (Cancelled)**